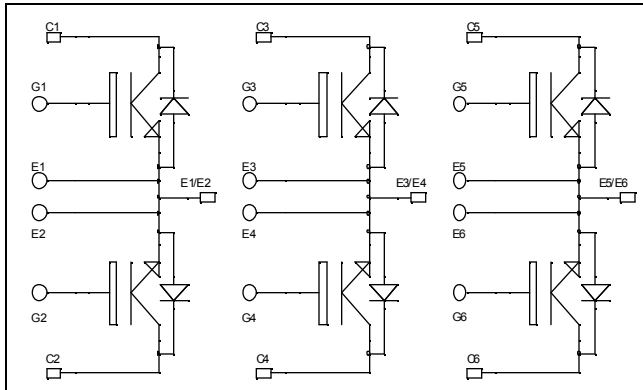


**Triple Dual Common Source
Trench + Field Stop IGBT®
Power Module**

**$V_{CES} = 600V$
 $I_C = 150A @ T_c = 80^\circ C$**

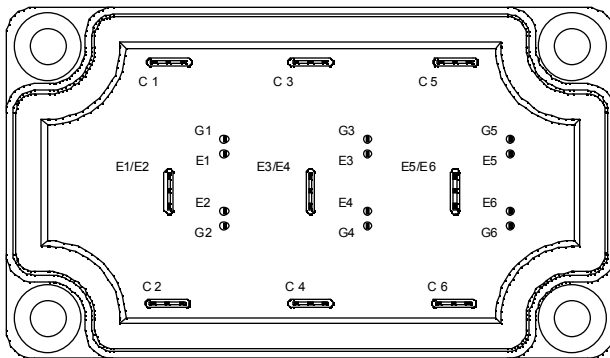


Application

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

Features

- Trench + Field Stop IGBT® Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration



Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCESat
- Very low (12mm) profile
- Each leg can be easily paralleled to achieve a dual common source configuration of three times the current capability
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	600	V
I_C	Continuous Collector Current	$T_c = 25^\circ C$	225
		$T_c = 80^\circ C$	150
I_{CM}	Pulsed Collector Current	$T_c = 25^\circ C$	350
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	480
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^\circ C$	300A @ 550V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}$, $V_{CE} = 600\text{V}$			250	μA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 150\text{A}$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	1.5 1.7	1.9	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C = 1.5\text{ mA}$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}$, $V_{CE} = 0\text{V}$			400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0\text{V}$		9200		pF
C_{oes}	Output Capacitance	$V_{CE} = 25\text{V}$		580		
C_{res}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		270		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		115		ns
T_r	Rise Time	$V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$		45		
$T_{d(off)}$	Turn-off Delay Time	$I_C = 150\text{A}$		225		
T_f	Fall Time	$R_G = 3.3\Omega$		55		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C)		130		ns
T_r	Rise Time	$V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$		50		
$T_{d(off)}$	Turn-off Delay Time	$I_C = 150\text{A}$		300		
T_f	Fall Time	$R_G = 3.3\Omega$		70		
E_{on}	Turn on Energy	$V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	0.85 1.5		mJ
E_{off}	Turn off Energy	$I_C = 150\text{A}$ $R_G = 3.3\Omega$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	4.1 5.3		mJ

Reverse diode ratings and characteristics

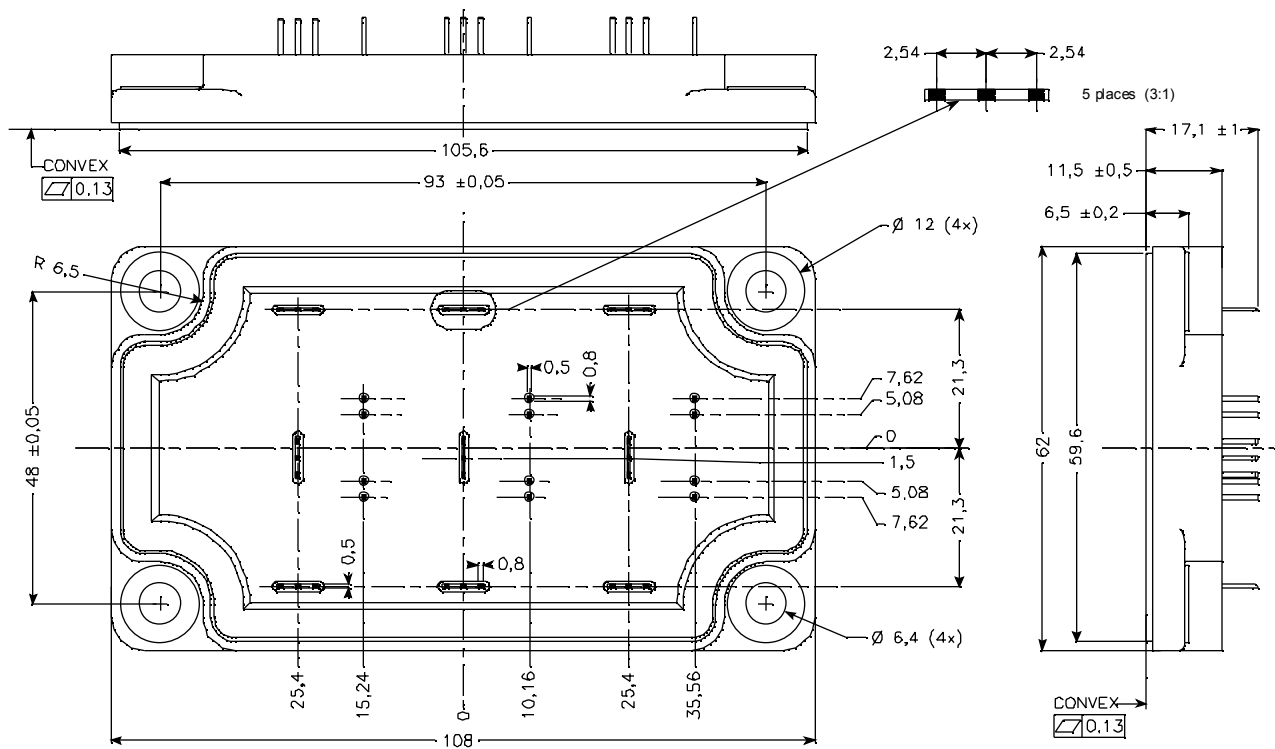
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		600			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 600\text{V}$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$		250 500	μA
I_F	DC Forward Current			150		A
V_F	Diode Forward Voltage	$I_F = 150\text{A}$ $V_{GE} = 0\text{V}$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	1.6 1.5	2	V
t_{rr}	Reverse Recovery Time		$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	130 225		ns
Q_{rr}	Reverse Recovery Charge	$I_F = 150\text{A}$ $V_R = 300\text{V}$ $di/dt = 3000\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	6.9 14.5		μC
E_r	Reverse Recovery Energy		$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	1.6 3.5		mJ

Thermal and package characteristics

Symbol Characteristic

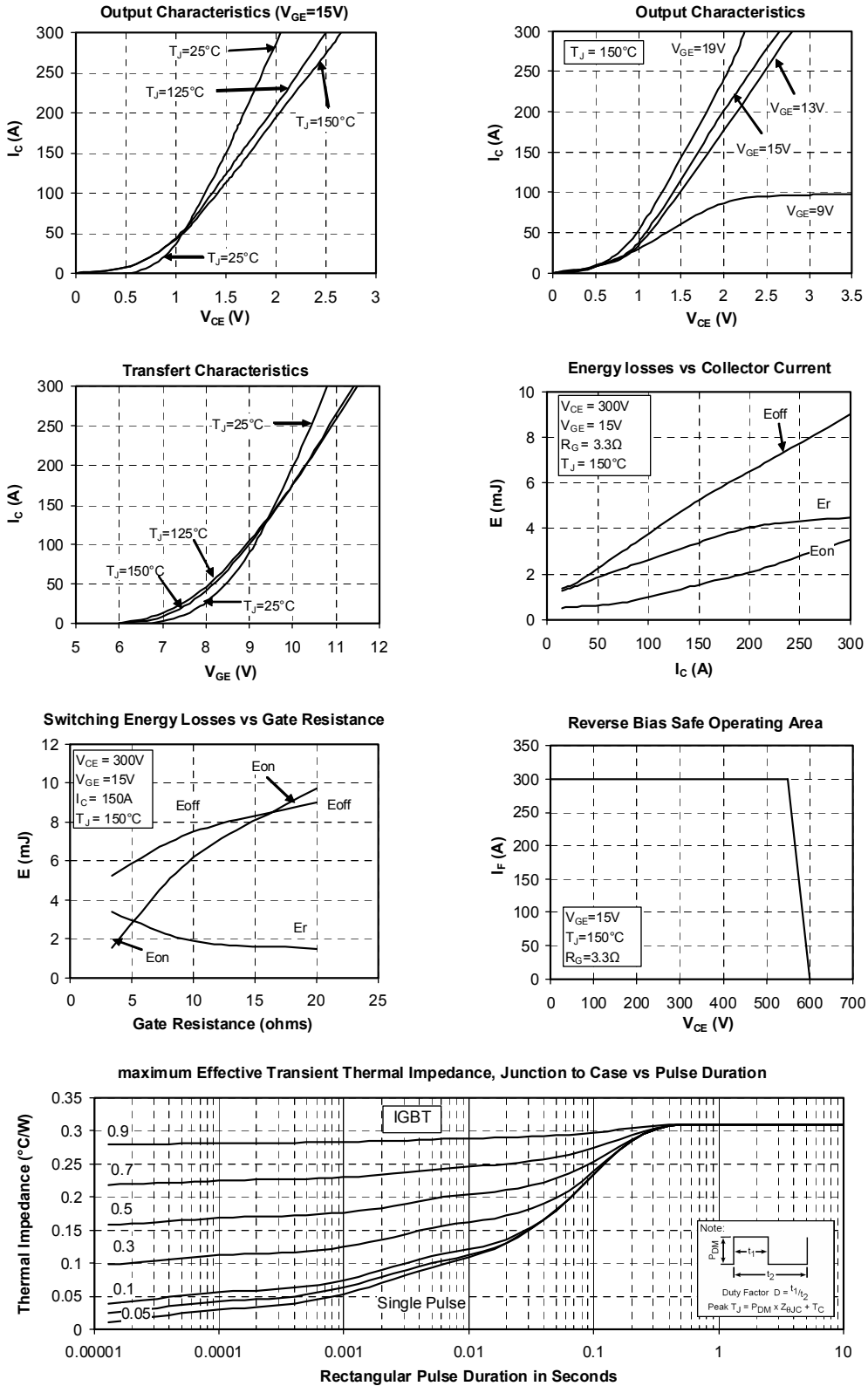
		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>	
R _{thJC}	Junction to Case Thermal Resistance	IGBT		0.31	°C/W	
		Diode		0.52		
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, I _{isol} <1mA, 50/60Hz	2500			V	
T _J	Operating junction temperature range	-40		175	°C	
T _{STG}	Storage Temperature Range	-40		125		
T _C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M6	3	5	N.m
Wt	Package Weight				250	g

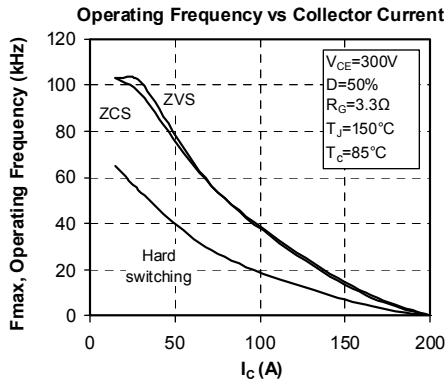
SP6-P Package outline (dimensions in mm)



See application note 1902 - Mounting Instructions for SP6-P (12mm) Power Modules on www.microsemi.com

Typical Performance Curve





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